

N-channel 80 V, 3.5 mΩ standard level MOSFET in I2PAK Rev. 02 — 19 April 2011 Product data

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in I2PAK package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switch

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. **Quick reference data**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	80	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 1</u>	<u>[1]</u>	-	-	120	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	338	W
Tj	junction temperature			-55	-	175	°C
Static char	acteristics						
Doon	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{100 \text{ Figure } 12}$		-	5	5.8	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 13</u>	[2]	- 3	3	3.5	mΩ
Dynamic cl	haracteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 75 \text{ A};$		-	27	-	nC
Q _{G(tot)}	total gate charge	V _{DS} = 40 V; see <u>Figure 14;</u> see <u>Figure 15</u>		-	139	-	nC
Avalanche	ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy			-	-	676	mJ

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- [1] Continuous current is limited by package.
- [2] Measured 3 mm from package.

2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	drain		
				mbb076 S
			$\overline{1}$ $\overline{2}$ $\overline{3}$	

SOT226 (I2PAK)

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PSMN3R5-80ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		5, (
Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	80	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	80	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	[1]	-	120	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	[1]	-	120	А
I _{DM}	peak drain current	pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C; see <u>Figure 3</u>		-	803	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	338	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drai	in diode					
I _S	source current	T _{mb} = 25 °C	[1]	-	120	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	803	А
Avalanche r	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; $V_{sup} \le 80$ V; R_{GS} = 50 Ω ; unclamped		-	676	mJ

[1] Continuous current is limited by package.

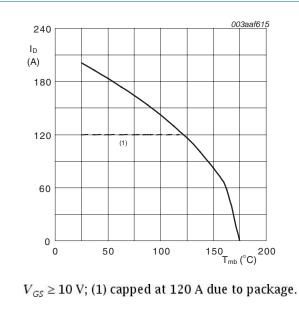
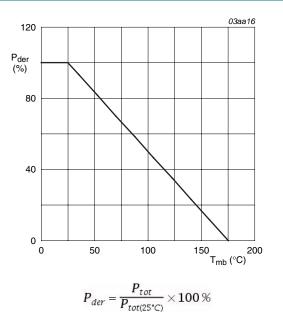
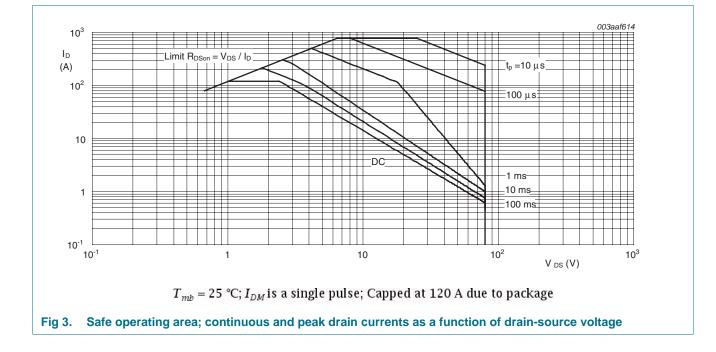


Fig 1. Continuous drain current as a function of mounting base temperature



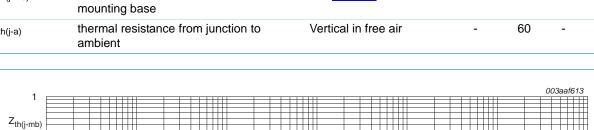


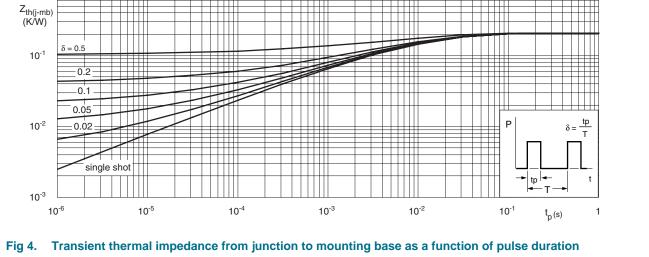
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5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 4	-	0.22	0.44	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W





6. Characteristics

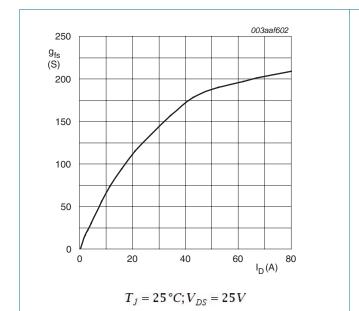
Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V _{(BR)DSS}	drain-source breakdown	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	73	-	-	V
	voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	80	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 10</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 10</u>	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
I _{DSS}	drain leakage current	$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	10	μΑ
		V_{DS} = 80 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μΑ
I _{GSS}	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
R _{DSon} drain-source on-state resistance		V_{GS} = 10 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 12</u>	-	7.2	8.4	mΩ
		V_{GS} = 10 V; I _D = 25 A; T _j = 100 °C; see <u>Figure 12</u>	-	5	5.8	mΩ
	$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \text{ T}_{j} = 25 \text{ °C};$ see Figure 13	<u>1]</u> _	3	3.5	mΩ	
R _G	internal gate resistance (AC)	f = 1 MHz	-	0.9	-	Ω
Dynamic c	haracteristics					
Q _{G(tot)} total gate charge		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	135	-	nC
		$I_D = 75 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$	-	139	-	nC
Q _{GS}	gate-source charge	see Figure 14; see Figure 15	-	51	-	nC
Q _{GS(th)}	pre-threshold gate-source charge		-	30	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	21	-	nC
Q _{GD}	gate-drain charge		-	27	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 40 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	5.8	-	V
C _{iss}	input capacitance	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	9961	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	847	-	pF
C _{rss}	reverse transfer capacitance		-	401	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 40 \text{ V}; \text{ R}_{L} = 0.53 \Omega;$	-	41	-	ns
t _r	rise time	V_{GS} = 10 V; $R_{G(ext)}$ = 10 Ω ; I_D = 75 A	-	43	-	ns
t _{d(off)}	turn-off delay time		-	109	-	ns
t _f	fall time		-	44	-	ns

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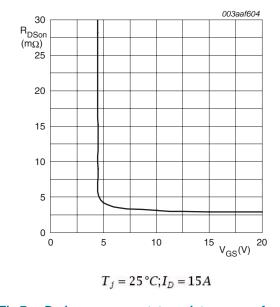
Table 6. Characteristicscontinued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dra	ain diode					
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 17</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = 100 \text{ A}/\mu\text{s};$	-	63	-	ns
Qr	recovered charge	$V_{GS} = 0 V; V_{DS} = 20 V$	-	121	-	nC

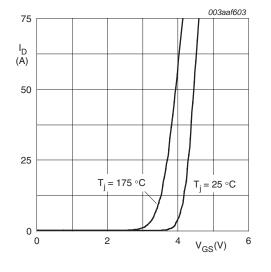
[1] Measured 3 mm from package.





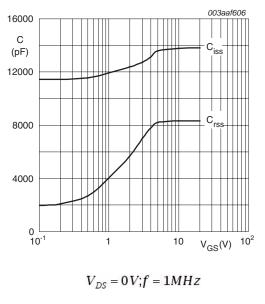










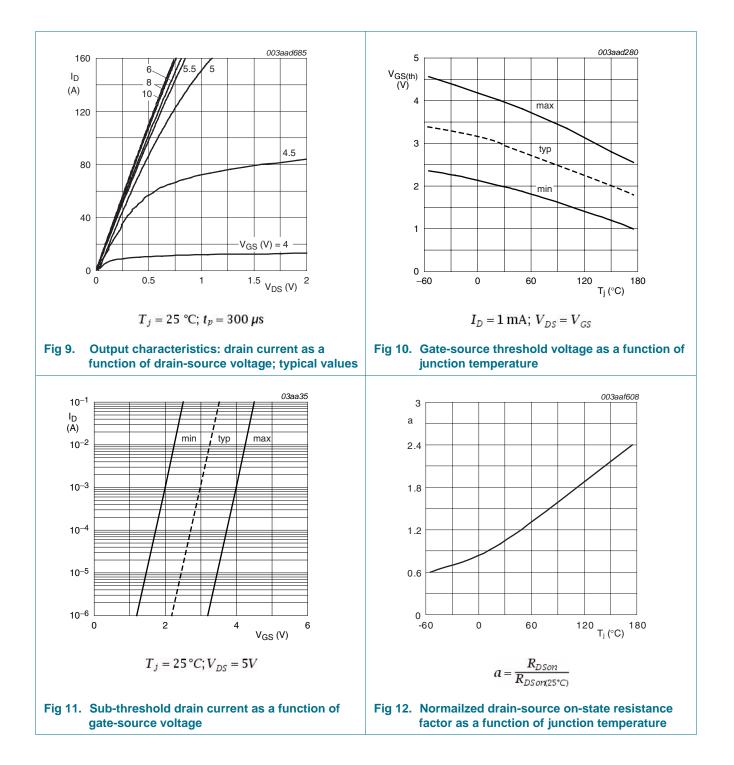




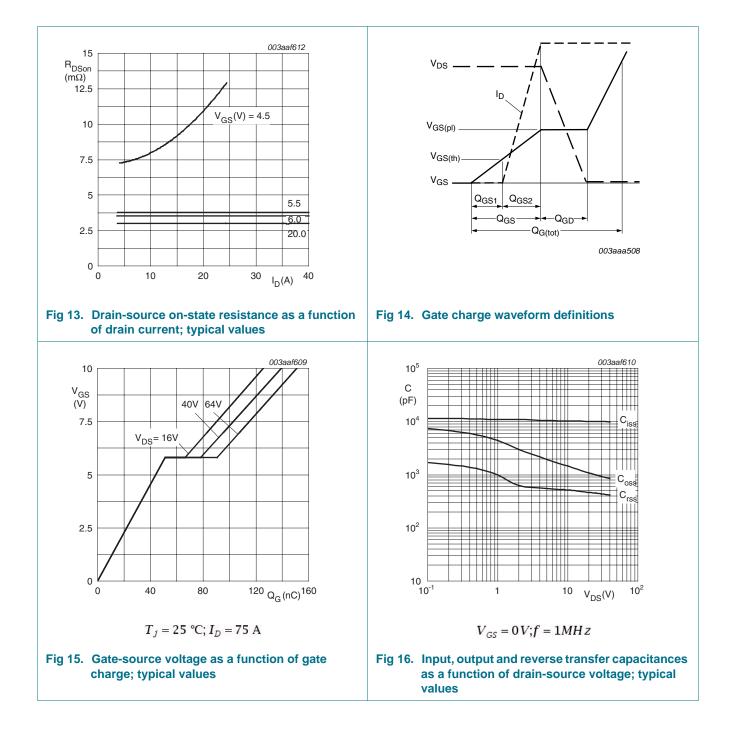
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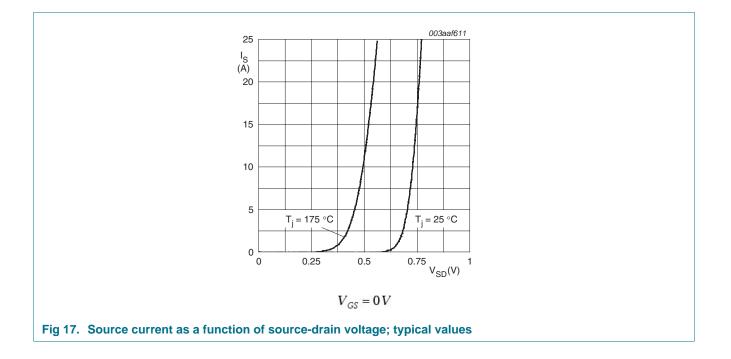
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7. Package outline

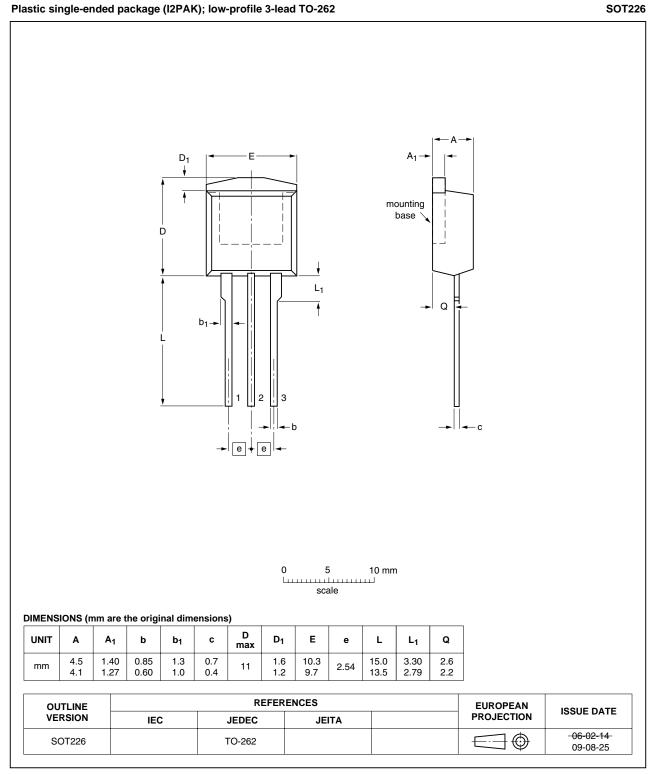


Fig 18. Package outline SOT226 (I2PAK)

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PSMN3R5-80ES

8. Revision history

Table 7. Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN3R5-80ES v.2	20110419	Product data sheet	-	PSMN3R5-80ES v.1
Modifications:	 Status change 	ed from objective to product.		
	 Various change 	ges to content.		
PSMN3R5-80ES v.1	20101224	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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Product data sheet

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